

(a) Book Chapter

1. **A. Haque**, “Self-consistent modeling of nano-scale MOS devices with high- K gate dielectrics considering wave function penetration effect,” in *Progress in Solid State Electronics Research* (ISBN: 978-1-60021-852-1), James P. Martingale, Editor, Nova Science Publishers, NY, USA, pp. 167-185, 2008 (Invited).

(b) Journal Papers

39. Md. M. Satter and **A. Haque**, “Modeling Effects of Interface Trap States on the Gate C-V Characteristics of MOS Devices on Alternative High-Mobility Substrates,” *Solid-State Electronics*, Vol. 54, No. 6, pp. 621-627, 2010.

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36. M. K. Ashraf, A. I. Khan, and **A. Haque**, “Wave function penetration effects on ballistic drain current in double gate MOSFETs fabricated on (100) and (110) silicon surfaces,” *Solid-State Electronics*, Vol. 53, No. 3, pp. 271-275, 2009.

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(c) Conference Papers

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